

**isc N-Channel MOSFET Transistor**

**IRFP360**

**FEATURES**

- Drain Current  $-I_D = 23A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 400V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 0.2 \Omega (\text{Max})$
- Fast Switching

**DESCRIPTION**

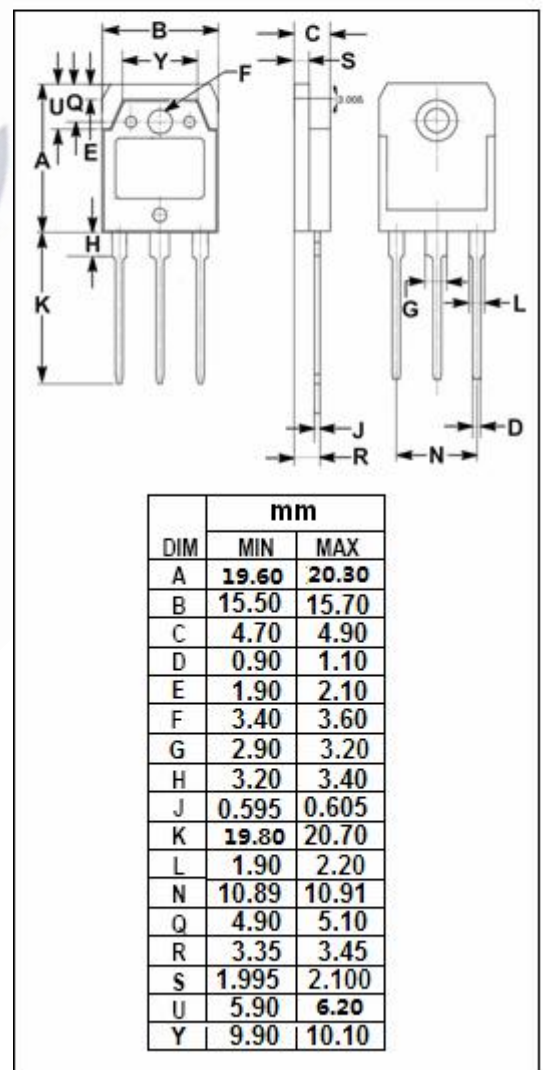
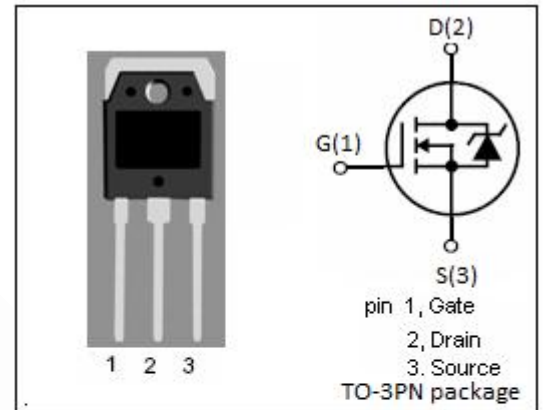
- Designed for use in switch mode power supplies and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	400	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	23	A
$I_{DM}$	Drain Current-Single Pulse	92	A
$P_D$	Total Dissipation @ $T_C = 25^\circ C$	250	W
$T_J$	Max. Operating Junction Temperature	-55~150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.50	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	30	$^\circ C/W$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	400		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA	2	4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 13A		0.2	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 400V; V <sub>GS</sub> = 0		250	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 23A; V <sub>GS</sub> = 0		1.8	V